# **74HC3GU04**

# Triple unbuffered inverter Rev. 5 — 2 October 2013

**Product data sheet** 

#### 1. **General description**

The 74HC3GU04 is a triple unbuffered inverter. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V<sub>CC</sub>.

#### **Features and benefits** 2.

- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low-power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - ♦ MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

## **Ordering information**

Table 1. **Ordering information** 

Type number	Package							
	Temperature range	Name	Description	Version				
74HC3GU04DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2				
74HC3GU04DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1				
74HC3GU04GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 $\times$ 2 $\times$ 0.5 mm	SOT996-2				

#### **Marking** 4.

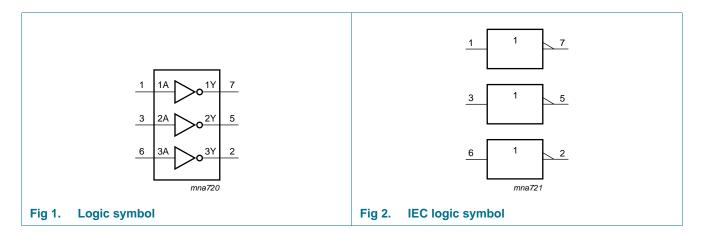
Table 2. **Marking** 

Type number	Marking code <sup>[1]</sup>
74HC3GU04DP	HU4
74HC3GU04DC	HU4
74HC3GU04GD	HU4

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

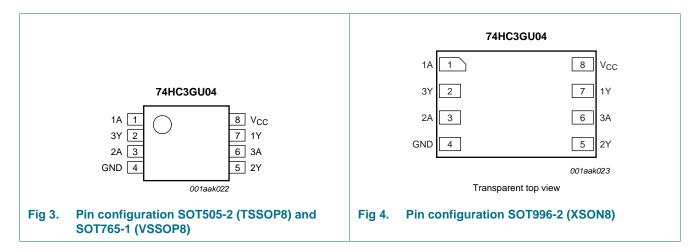


# 5. Functional diagram



# 6. Pinning information

## 6.1 Pinning



## 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A, 3A	1, 3, 6	data input
1Y, 2Y, 3Y	7, 5, 2	data output
GND	4	ground (0 V)
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

Table 4. Function table [1]

Input	Output
nA	nY
L	Н
H	L

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
I <sub>OK</sub>	output clamping current	$V_{O}$ < $-0.5$ V or $V_{O}$ > $V_{CC}$ + $0.5$ V	<u>[1]</u> -	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	<u>[1]</u> -	±25	mA
I <sub>CC</sub>	quiescent supply current		<u>[1]</u> -	50	mA
I <sub>GND</sub>	ground current		<u>[1]</u> –50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] _	300	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# 9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		2.0	5.0	6.0	V
VI	input voltage		0	-	$V_{CC}$	V
Vo	output voltage		0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	ns/V
		V <sub>CC</sub> = 4.5 V	-	1.67	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	ns/V

<sup>[2]</sup> For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K. For XSON8 package: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## 10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			–40 °C t	Unit	
			Min	Typ[1]	Max	Min	Max	
$V_{IH}$	HIGH-level input	V <sub>CC</sub> = 2.0 V	1.7	1.1	-	1.7	-	V
	voltage	V <sub>CC</sub> = 4.5 V	3.6	2.4	-	3.6	-	V
		V <sub>CC</sub> = 6.0 V	4.8	3.1	-	4.8	-	V
V <sub>IL</sub>	LOW-level input	$V_{CC} = 2.0 \text{ V}$	-	0.9	0.3	-	0.3	V
	voltage	V <sub>CC</sub> = 4.5 V	-	2.1	0.9	-	0.9	V
		V <sub>CC</sub> = 6.0 V	-	2.9	1.2	-	1.2	V
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH}$ or $V_{IL}$						
	voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 \text{ V}$	5.9	6.0	-	5.9	-	V
		$I_O = -4.0 \text{ mA}$ ; $V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output	$V_I = V_{IH}$ or $V_{IL}$						
	voltage	$I_{O} = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±1.0	-	±1.0	μΑ
I <sub>CC</sub>	supply current	per input pin; $V_1 = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	10	-	20	μА
Cı	input capacitance		-	3.0	-	-	-	pF

<sup>[1]</sup> All typical values are measured at  $T_{amb}$  = 25 °C.

# 11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 6.

Symbol	Parameter	Conditions		–40 °C to +85 °C			-40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 5	[2]						'
		V <sub>CC</sub> = 2.0 V		-	13	75	-	90	ns
		V <sub>CC</sub> = 4.5 V		-	6	15	-	18	ns
		V <sub>CC</sub> = 6.0 V		-	5	13	-	15	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 6.

Symbol	Parameter	Conditions		–40 °C to +85 °C			-40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t <sub>t</sub>	transition time	nY; see Figure 5	3]						
		$V_{CC} = 2.0 \text{ V}$		-	18	95	-	125	ns
		$V_{CC} = 4.5 V$		-	6	19	-	25	ns
		V <sub>CC</sub> = 6.0 V		-	5	16	-	20	ns
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$	<u>4]</u>	-	5	-	-	-	pF

- [1] All typical values are measured at  $T_{amb} = 25$  °C.
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [3]  $t_t$  is the same as  $t_{TLH}$  and  $t_{THL}$ .
- [4]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

#### 12. Waveforms

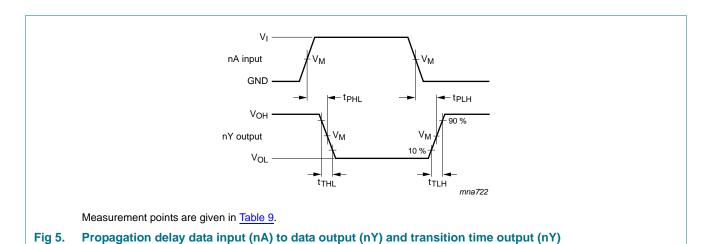
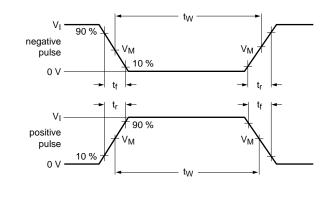
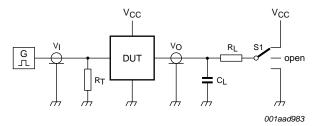


Table 9. Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74HC3GU04	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$





Test data is given in Table 10.

Definitions for test circuit:

 $R_{T}$  = Termination resistance should be equal to output impedance  $Z_{o}$  of the pulse generator.

 $C_L$  = Load capacitance including jig and probe capacitance.

R<sub>L</sub> = Load resistance.

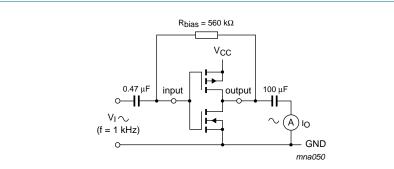
S1 = Test selection switch.

Fig 6. Test circuit for measuring switching times

Table 10. Test data

Туре	Input		Load	S1 position	
	VI	t <sub>r</sub> , t <sub>f</sub>	C <sub>L</sub>	$R_L$	t <sub>PHL</sub> , t <sub>PLH</sub>
74HC3GU04	GND to $V_{CC}$	≤ 6 ns	50 pF	1 kΩ	open

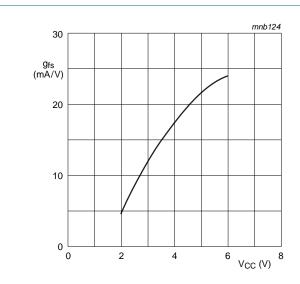
## 12.1 Additional characteristics



$$g_{fs} = \frac{\Delta I_O}{\Delta V_I}$$

Vo is constant.

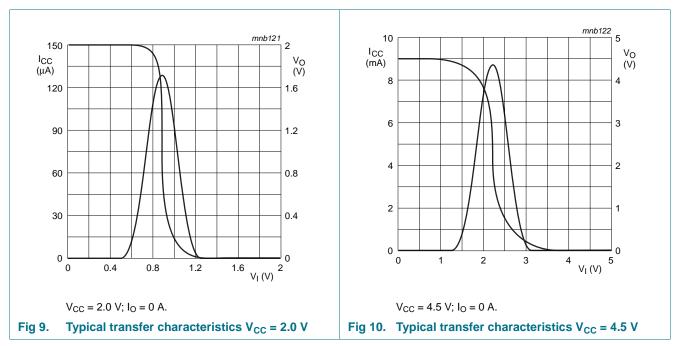
Fig 7. Test set-up for measuring forward transconductance

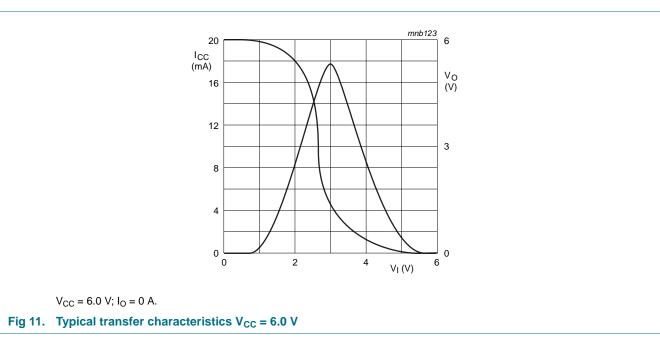


 $T_{amb}$  = 25 °C.

Fig 8. Typical forward transconductance as a function of supply voltage

# 13. Typical transfer characteristics





# 14. Application information

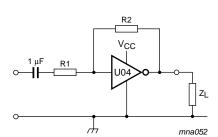
Some applications for the 74HC3GU04 are:

- Linear amplifier (see Figure 12)
- Crystal oscillator (see Figure 14).

74HC3GU04

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Remark: All values given are typical values unless otherwise specified.



 $Z_L > 10 \text{ k}\Omega$ .

 $R1 \geq 3 \ k\Omega.$ 

 $R2 \le 1 M\Omega$ .

Open loop amplification:  $A_{OL} = 20$  (typical).

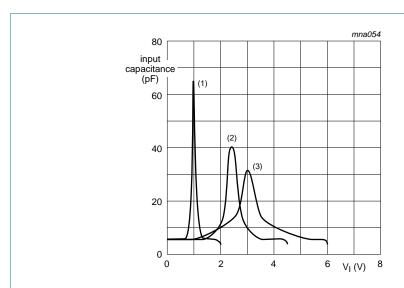
$$\mbox{Voltage amplification:} \quad A_V = -\frac{A_{OL}}{I + \frac{R\,I}{R2}(I + A_{\rm OL})} \,.$$

 $V_{o(p-p)} = V_{CC} - 1.5 \text{ V}$  centered at  $0.5 \times V_{CC}$ .

Unity gain bandwidth product is 5 MHz (typical).

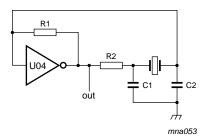
Input capacitance see Figure 13.

Fig 12. Linear amplifier application



- (1)  $V_{CC} = 2.0 \text{ V}.$
- (2)  $V_{CC} = 4.5 \text{ V}.$
- (3)  $V_{CC} = 6.0 \text{ V}.$

Fig 13. Typical input capacitance as a function of the input voltage



Test data is given in Table 11 and Table 12.

C1 = 47 pF (typical).

C2 = 22 pF (typical).

R1 = 1 M $\Omega$  to 10 M $\Omega$  (typical).

R2 optimum value depends on the frequency and required stability against changes in  $V_{CC}$  or average minimum  $I_{CC}$  ( $I_{CC} = 2$  mA at  $V_{CC} = 3.0$  V and f = 1 MHz)

Fig 14. Crystal oscillator application

Table 11. External components for resonator (f < 1 MHz)

Frequency	R1	R2	C1	C2
10 kHz to 15.9 kHz	$2.2~\text{M}\Omega$	220 kΩ	56 pF	20 pF
16 kHz to 24.9 kHz	2.2 MΩ	220 kΩ	56 pF	10 pF
25 kHz to 54.9 kHz	2.2 MΩ	100 kΩ	56 pF	10 pF
55 kHz to 129.9 kHz	2.2 MΩ	100 kΩ	47 pF	5 pF
130 kHz to 199.9 kHz	2.2 MΩ	47 kΩ	47 pF	5 pF
200 kHz to 349.9 kHz	2.2 MΩ	47 kΩ	47 pF	5 pF
350 kHz to 600 kHz	2.2 ΜΩ	47 kΩ	47 pF	5 pF

Table 12. Optimum value for R2

Frequency	R2	Optimum		
3 kHz	$2.0~\text{k}\Omega$	minimum required I <sub>CC</sub>		
	8.0 kΩ	minimum influence due to change in V <sub>CC</sub>		
6 kHz	1.0 kΩ	minimum required I <sub>CC</sub>		
	$4.7~\mathrm{k}\Omega$	minimum influence by V <sub>CC</sub>		
10 kHz	$0.5~\mathrm{k}\Omega$	minimum required I <sub>CC</sub>		
	2.0 kΩ	minimum influence by V <sub>CC</sub>		
14 kHz	$0.5~\mathrm{k}\Omega$	minimum required I <sub>CC</sub>		
	2.0 kΩ	minimum influence by V <sub>CC</sub>		
> 14 kHz	replace R2 by C3 = 35 pF (typical)			

## 15. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

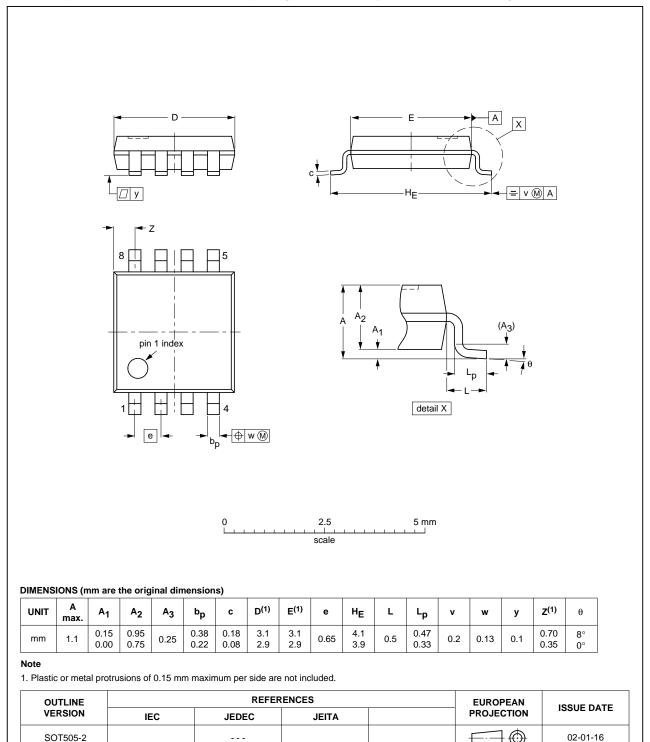
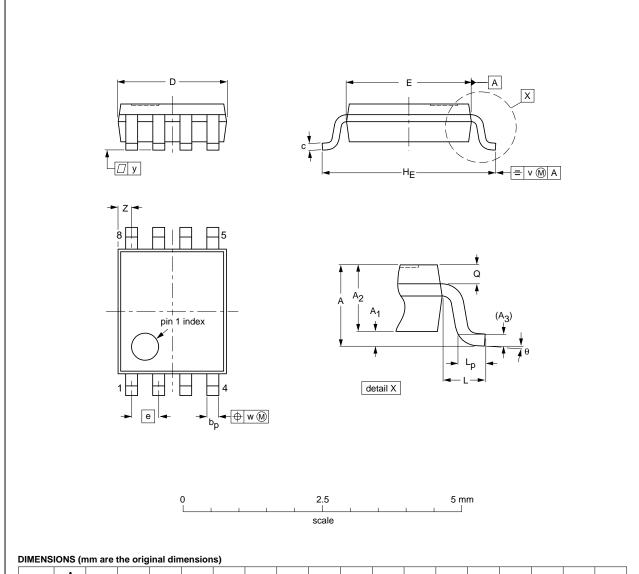


Fig 15. Package outline SOT505-2 (TSSOP8)

#### VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	А3	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

#### Notes

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.
   Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	IEC JEDEC JEIT				
SOT765-1		MO-187				02-06-07

Fig 16. Package outline SOT765-1 (VSSOP8)

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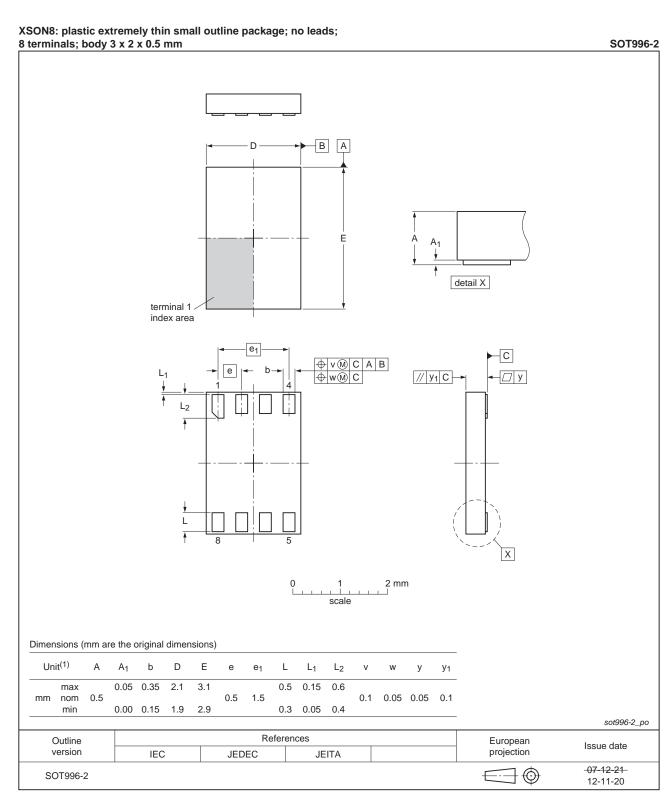


Fig 17. Package outline SOT996-2 (XSON8)

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74HC3GU04

**Triple unbuffered inverter** 

## 16. Abbreviations

#### Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 17. Revision history

#### Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC3GU04 v.5	20131002	Product data sheet	-	74HC3GU04 v.4
Modifications:	<ul> <li>For type nun</li> </ul>	nber 74HC3GU04GD XSON8L	J has changed to XS	ON8.
74HC3GU04 v.4	20100111	Product data sheet	-	74HC3GU04 v.3
Modifications:	<ul> <li>Marking cod</li> </ul>	e for 74HC3GU04DP package	changed from HU04	to HU4
74HC3GU04 v.3	20090511	Product data sheet	-	74HC3GU04 v.2
74HC3GU04 v.2	20031126	Product specification	-	74HC3GU04 v.1
74HC3GU04 v.1	20030818	Product specification	-	-

## 18. Legal information

#### 18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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#### Triple unbuffered inverter

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**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

#### 18.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

#### 19. Contact information

For more information, please visit: <a href="http://www.nxp.com">http://www.nxp.com</a>

For sales office addresses, please send an email to: salesaddresses@nxp.com

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#### **Triple unbuffered inverter**

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